钇对掺饵多孔硅体系1.54μm发光的增强作用

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摘要 首次报道了用恒电位电解法将饵、钇共掺入多孔硅(porous silicons, PS)中,经高温退火处理后,观察到了在近红外区(1.54 μm)室温下较强的光致发光 (photoluminescence, PL),并与掺饵多孔硅(erbiumdoped porous silicon, PS:Er)做了比较,发现钇的共掺入对掺饵多孔硅体系1.54 μm发射起了增强作用。研究了饵、钇共掺杂多孔硅(erbium and yttrium co-doped porous silicon, PS:Er, Y)光致发光强度随温度的变化,发现PS:Er与Si:Er材料相似,有较强的 温度猝灭效应,而PS:Er,Y体系的PL强度随温度升高趋于平稳,且有增强的趋势, 受温度影响不明显,并初步探讨了其发光机制。 关键词 <u>硅</u> 铒 <u>钇</u> <u>掺杂</u> 光致发光 <u>电解</u> <u>荧光猝灭剂</u>

Emhanced 1.54 µm Luminescence from Erbium and Yttrium Co-doped Porous Silicon

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Abstract Fabrication of erbium (Er) and yttrium (Y) co-doped porous silicon (PS:Er,Y) is firstly reported. Enhancement of Er-related photoluminescence at 1.54 μ m has been achieved by the co-doping of Y~ (3+) . The dependence of photoluminescence intensity on temperature was investigated. Luminescence quenching was observed for PS: Er, similar to that for Si:Er, while 1.54 μ m luminescence intensity from PS:Er,Y was found to increase a little when the photoluminescence spectra were measured at a higher temperature. A possible enhanced photoluminescence mechanism was proposed.

Key words <u>SILICON</u> <u>SILICON</u> <u>YTTRIUM</u> <u>DOPE</u> <u>PHOTOLUMINESCENCE</u> <u>ELECTROLYSIS</u> FLUORESCENCE QUENCHER

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